

Micro Power PIR signal Op Amp

Patent Number

Taiwan: M455864

China: ZL 2013 2 0099927.6

General Description

TTY020 is a micro power CMOS chip IC design to detect PIR signal control IC. PIR sensor detect infrared power variation induced by the motion of a human body and transforms it to a voltage variation signal. TTY020 use unique **variation window** technology and have **warm up fast** steady time, low power consumption, few external components needed, high sensitivity, steady work feature. The device wide can be used to need PIR controller IC product

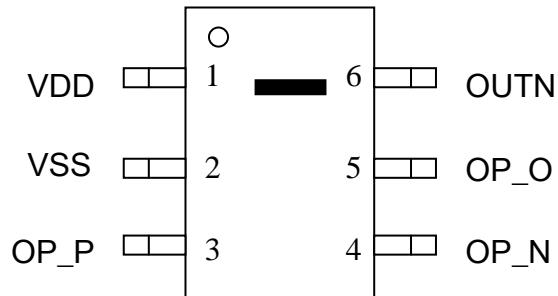
Feature

- Operating voltage range : 2.4V ~ 5.5V °
- Operating current, no load : 25uA@VDD=3V °
- Provide warm up fast steady time : 10sec@VDD=3V °
- During warm up fast steady time, OUTN active low °
- Unique variation window detect technology can improve noise ability °
- Simple application circuit °
- 6 PIN package (SOT23-6) °

Application

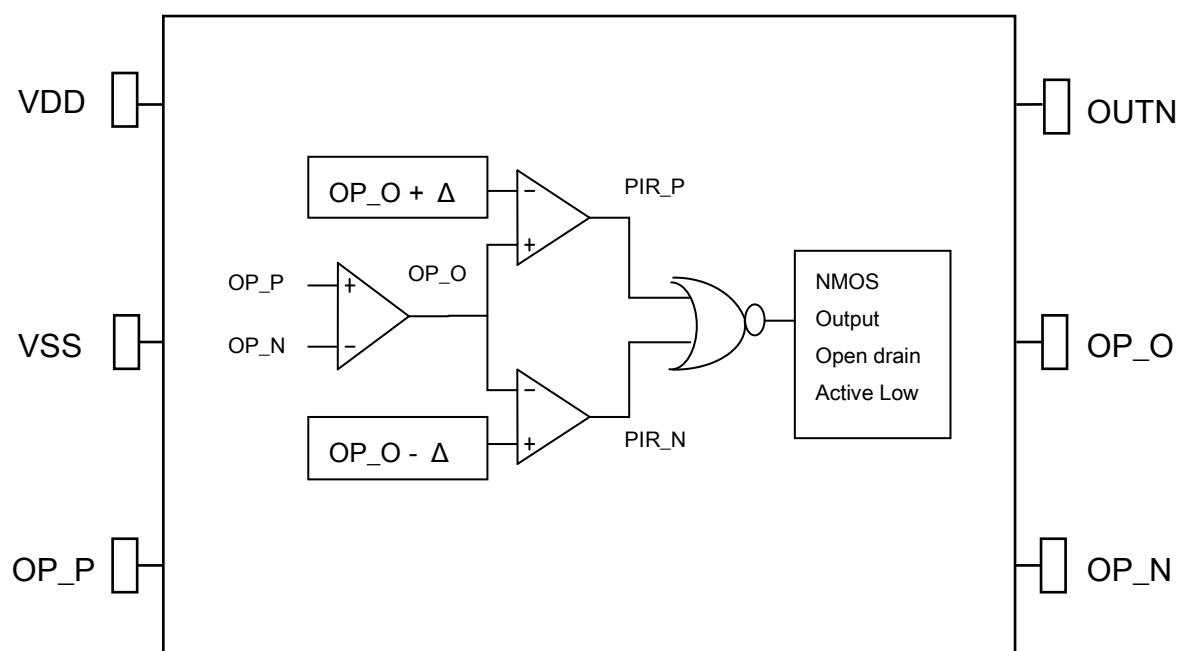
- Human body induce lamp
- Need PIR controller system

IC Package



SOT23-6

Block Diagram



* Δ : PIR variation window

Pin Define

| Pin No. | Pad Name | I/O Type | Pad Description |
|---------|----------|----------|---|
| 1 | VDD | P | Positive power supply : 2.4 V ~ 5.5V |
| 2 | VSS | P | Negative power supply, ground |
| 3 | OP_P | I | OP AMP(+), input pin |
| 4 | OP_N | I | OP AMP(-), input pin |
| 5 | OP_O | O_A | OP AMP (out), output pin |
| 6 | OUTN | OD | Open Drain output(have no Diode protective circuit), active low |

Pin Type

| | |
|-----|--|
| I | CMOS input |
| O_A | ANALOG output |
| OD | NMOS open drain output, have no diode protective circuit |
| P | Power / Ground |

Electrical Characteristics

- **Absolute Maximum Ratings**

| Parameter | Symbol | Conditions | Value | Unit |
|---|------------------|----------------------|---|------|
| Operating Temperature | T _{OP} | — | -20 ~ +70 | °C |
| Storage Temperature | T _{STG} | — | -50 ~ +125 | °C |
| Power Supply Voltage | V _{DD} | T _a =25°C | V _{SS} -0.3 ~ V _{SS} +5.5 | V |
| Input Voltage | V _{IN} | T _a =25°C | V _{SS} -0.3 ~ V _{DD} +0.3 | V |
| Note : VSS symbolizes for system ground | | | | |

- **DC/AC Characteristics :** (Test condition at room temperature=25°C)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--------------------------|-----------------|---|------|------|------|------|
| Operating Voltage | V _{DD} | | 2.4 | 5.0 | 5.5 | V |
| System oscillator | Fosc | Fosc=16Khz ± 15% @VDD=3.3V | 13.6 | 16.0 | 18.4 | KHz |
| Warm up fast steady time | SPT | VDD=3.3V | 8.5 | 10 | 11.5 | sec |
| Operating Current | I _{OP} | VDD=3.3V No Load | | 25 | 35 | uA |
| | | | | | | |
| Output Port Sink Current | I _{OL} | VDD=3.3V, V _{OL} =0.5V Pin : OUTN | - | 25 | - | mA |
| Output Port OP_O Current | I _{OL} | VDD=3.3V, V _{OP_O} =1.5V | - | 250 | - | uA |
| | I _{OH} | VDD=3.3V, V _{OP_O} =1.5V | - | 250 | - | uA |

Function Description

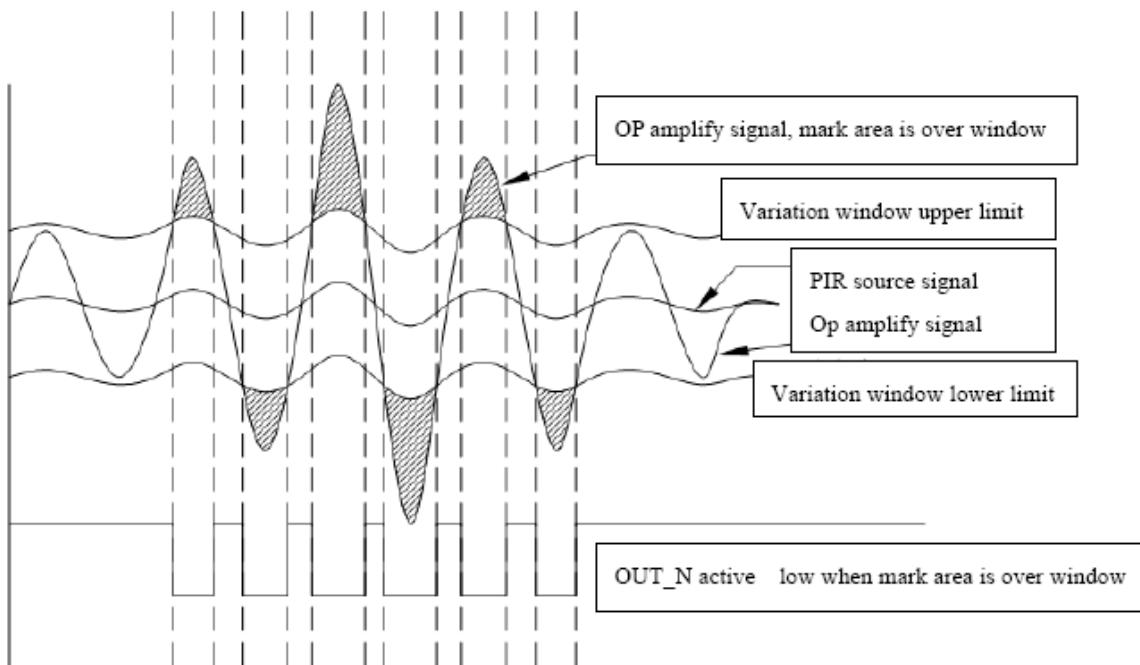
1. Package Type :

SOT23-6

2. Power ON initial

- (1). Provide the first OP warm up fast steady time 10 sec after Power On .
- (2). During warm up fast steady time, OUTN active low .

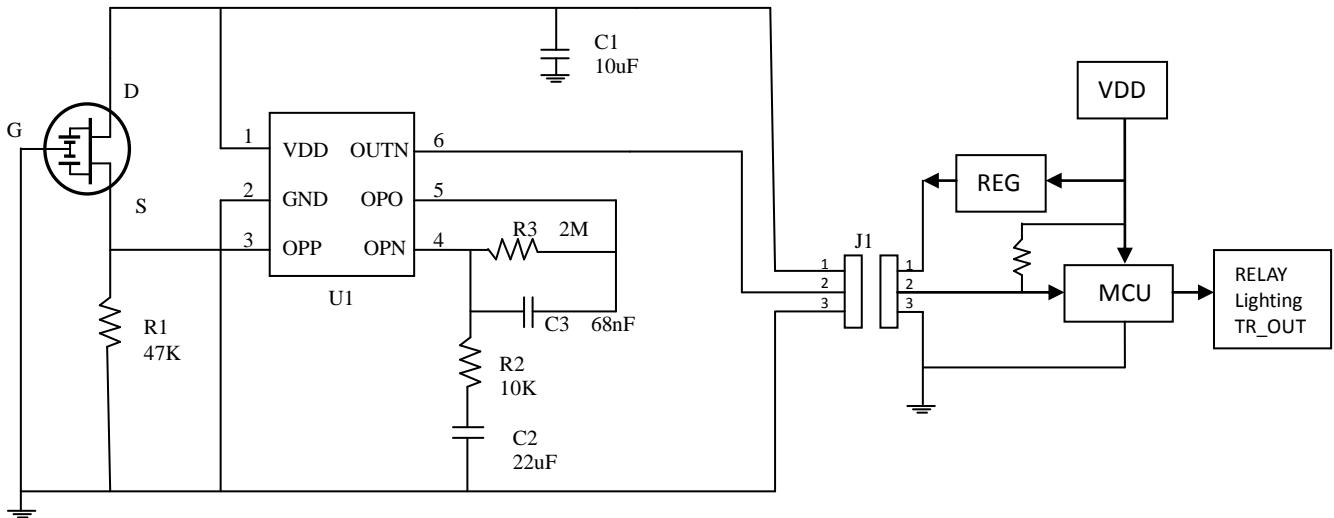
3. PIR signal trigger recognize



Note:

- (1). If OP amplify signal is over variation window, then OUTN active low, otherwise OUTN is high impedance
- (2). OUTN signal output debounce 8mS.

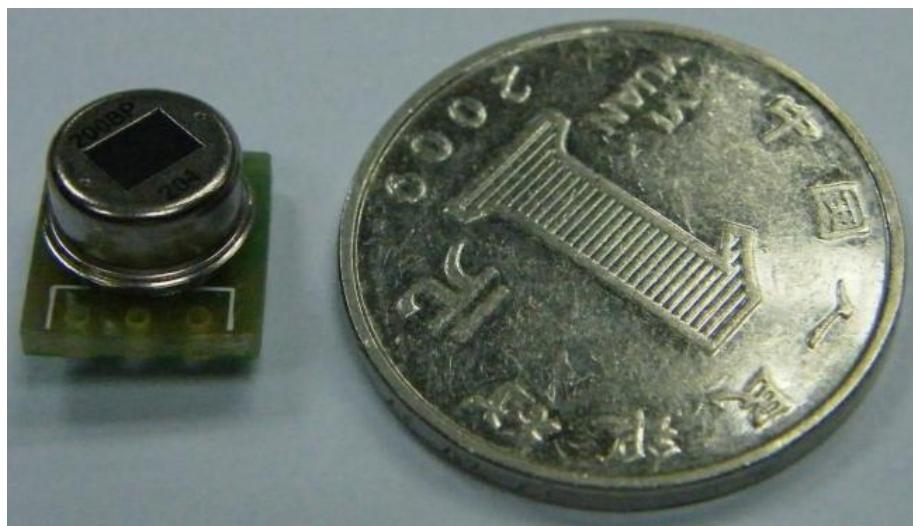
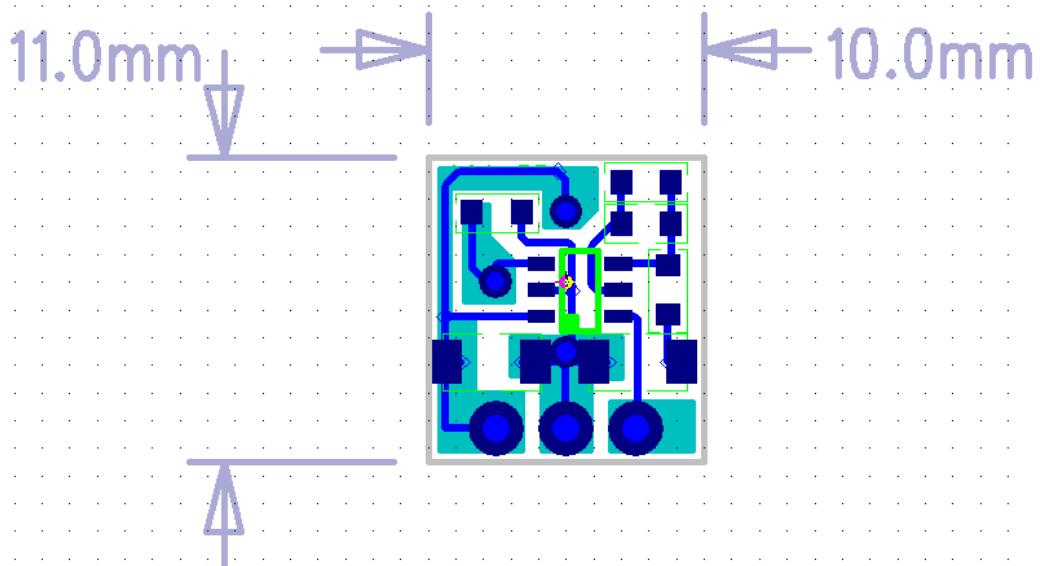
Application Circuit



Note:

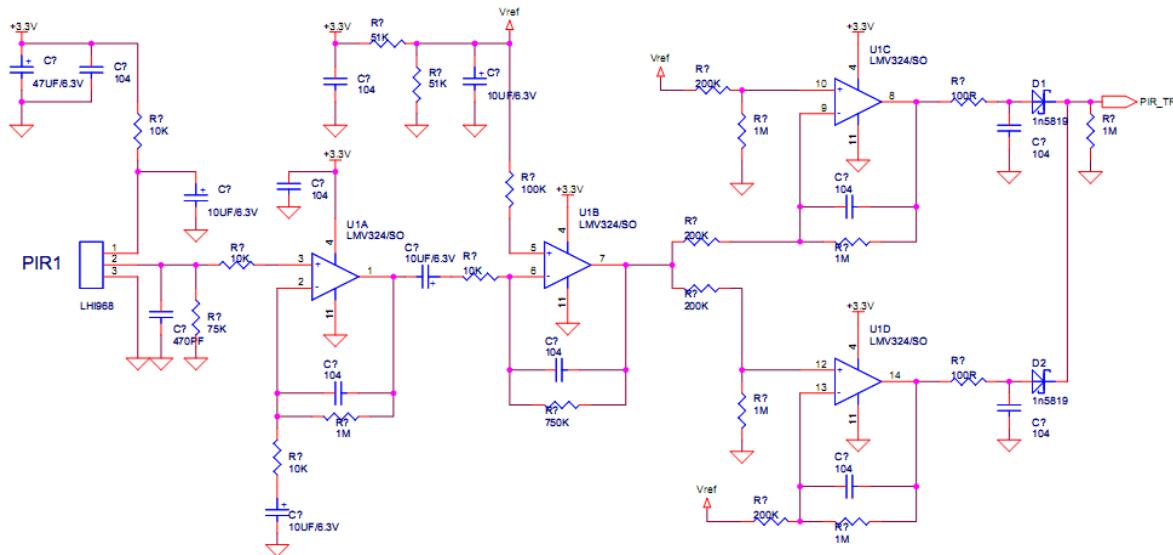
- (1). R1=47KΩ can be selected range 47KΩ ~300KΩ , if the value of R1 use higher , then PIR Sensor statics current will be smaller.
- (2). R3=2MΩ don't more than 3MΩ , can be selected to adjust sensitivity, if the value of R3 use higher, then OP amplifier gain higher.
- (3). R2 < 1Ω ~50KΩ can be selected to adjust sensitivity, if the value of R2 use smaller, then OP amplifier gain higher.
- (4). C3=68nF~100nF has low pass filer effect, only the frequency <10Hz signal can be amplified, $F=1/(2\pi RC)$
- (5). C2=10uF~47uF filter out DC signal capacitor, has high pass filer effect, only the frequency >0.1Hz signal can be amplified, $F=1/(2\pi RC)$. the C2 must use ceramic capacitor that has smaller leakage current, don't use electrolytic capacitor that has higher leakage current.
- (6). C1=10uF power decoupling capacitance.
- (7). OP_P DC voltage=0.7V depend on PIR Sensor specification, normal range 0.4V~1.1V, suggest to use higher consistency PIR Sensor for S node voltage.
- (8). If OP_O voltage is over PIR Δ variation window, then OUTN active low, otherwise OUTN is high impedance
- (9). Application be requested to provide steady power, use LDO to regulate voltage 2.4V~5V, and wire is as shorter as possible
- (10). OUTN is open drain output, can be connect to MCU I/O directly, (**MCU device need an internal or external pull-high resister 51KΩ ~300KΩ**), don't drive the larger current load directly, for example LED... etc.
- (11). OUTN signal output has debounce 8mS.

Practical Example



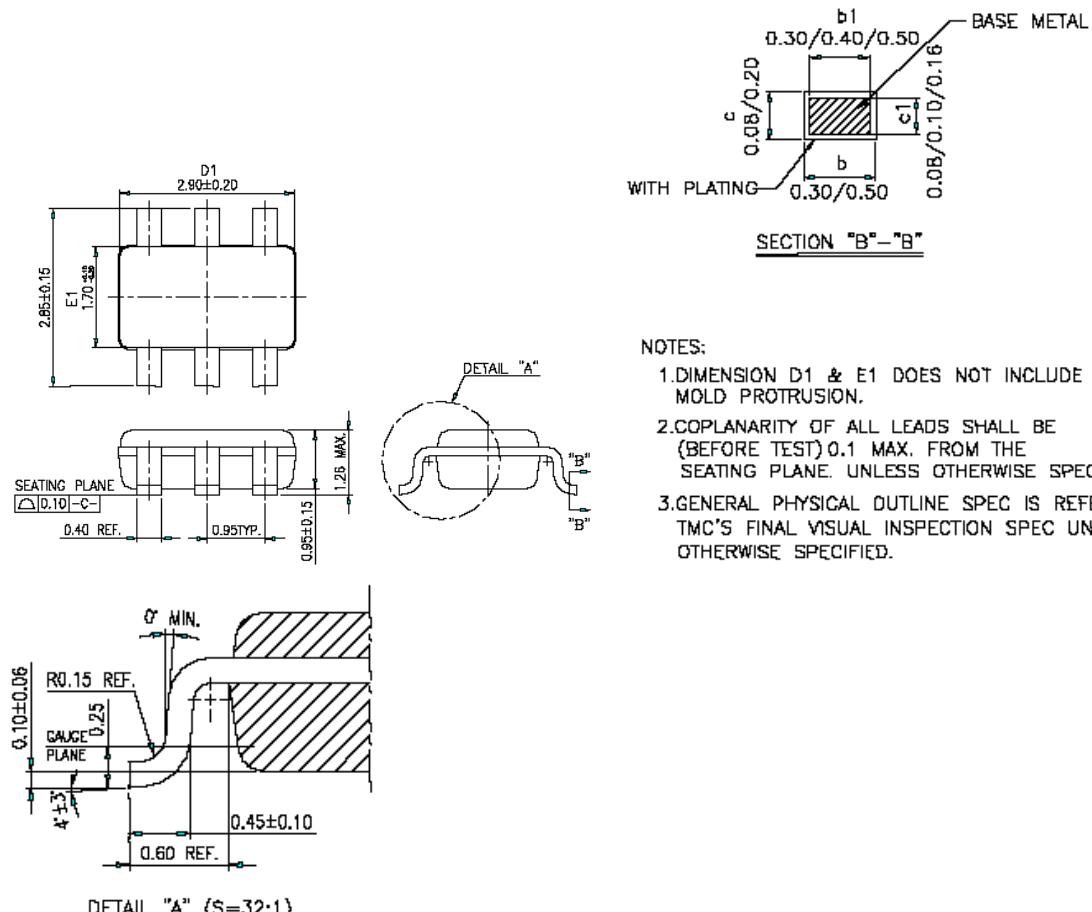
Contrast with LM324

The PIR signal amplification circuit which be build by LM324 has complex peripheral component. It add each component and therefore add each risk. PCB wire the more much, the more larger for noise that reduce stability of system. TTY020 amplification circuit only have 4 component for resistor and capacitor, it heavily reduce risk on application component and PCB area can be made very small size, so can avoid external interference and improve circuit working stability for long time.



Package Type

SOT23-6



Order Information

1. Package form : TTY020-CA6
2. Chip form : —
3. Wafdebase : ---

Revise History

1. 2013/12/17 - Original version : V_1.0
2. 2014/06/10 - Modify version : V_1.1
3. 2016/01/26 - Modify version : V_1.2